

Amendments to the Specification

Please replace paragraph [0047] with the following rewritten paragraph:

[0047] Fig. 4 is a schematic of a driving thin-film transistor and a light-emitting element according to a second exemplary embodiment of the present invention. As shown in Fig. 4, in the driving thin-film transistor 21, the lightly doped regions 27 are provided in both the source region 24 and the drain region 25. The lightly doped region 27 in the drain region 25 is longer than the lightly doped region 27 in the source region 24, resulting in an asymmetrical LDD structure. As shown in Fig. 4, an area of a cross section of the source region 24 is approximately equal to an area of a cross section of the drain region 25, when the cross sections are taken along a plane generally perpendicular to a mounting surface of the thin-film transistor. In the driving thin-film transistor 21 shown in Fig. 4, the same reference numerals are given to components corresponding to those of the first exemplary embodiment, and detailed descriptions of the common portions are omitted.